Amendments to the Specification:

Please amend the specification as follows:

Page 11, para 33:

[0033] Figure 1 is a simplified cross-sectional view of an exemplary brush scrubbing-proximity cleaning and/or drying system 100, in accordance with one embodiment of the present invention. The brush scrubbing and proximity cleaning and/or drying system 100 includes a chamber 104 disposed above a fluid handling system 106, front and back proximity heads 110a and 110b secured to an actuating component 114, and a system controller 116. Front and back proximity heads 110a and 110b are connected to the actuating component 114 by a front arm and a back arm 126a and 126b, respectively. In one embodiment, the actuating component 114 can be a motor, however, in a different embodiment, the actuating component 114 can be any component capable of moving front and back arms 126a and 126b. Furthermore, it must be appreciated by one of ordinary skill in the art that different mechanics and engineering can be implemented to move front and back arms ~~112a~~ 126a ~~and~~ ~~112b~~ 126b and thus front and back proximity heads 110a and 110b into and out of the chamber 104.

Page 15, para 43:

[0043] Proceeding to the simplified, cross sectional view shown in Figure 2A, brush scrubbing the wafer backside 102b using the brush 122 in the brush scrubbing proximity cleaning and/or drying system 100 of the present invention is provided, in accordance with one embodiment of the present invention. Cleaning the wafer backside 102b is commenced by bringing the brush 122 into contact with the wafer backside 102b. In one embodiment, the brush 122 originally defined in the vicinity of the chamber bottom wall 104a at a height H1 is

moved to a height H2 in a direction 136. At this point, brush 138 and thus nodules 124 of the brush ~~122~~ 138 are applied to the wafer backside 102b as the brush 122 rotates in a rotation direction 122 and is moved across the wafer backside 102b in an arc-like direction 142 as the wafer 102 is rotated in the rotation direction 140.

Page 16, para 46:

[0046] In one exemplary embodiment, the brush 122 can be mounted on a brush core secured to a shaft. As shown, the outer surface of the brush 122 is covered with a plurality of nodules ~~142~~ 144 that are brought into contact with the wafer backside 102b during the brush scrubbing operation so as to remove the contaminants 145 from over the wafer backside 102b.

Page 17, para 48:

[0048] A brush core 123 is connected to a fluid inlet designed to supply brush scrubbing chemistry 121 into the brush cores 123 through a supply tube 134 disposed inside a shaft ~~142~~ 143. In one example, the shaft ~~142~~ 143 is used to apply the brush 122 onto the wafer backside 102b and move the brush 122 between heights H1 and H2. Although not shown, brush core 123 has a plurality of holes thereon, allowing brush scrubbing chemistry to exit the brush core 123 so as to flush the brush 122.

Page 19, para 55:

[0055] Proceeding to the simplified cross sectional view of the brush scrubbing proximity cleaning and/or drying system 100 illustrated in Figure 3A, proximity cleaning and/or drying the wafer front side 102a and wafer backside 102b employing a chemistry compatible with the brush scrubbing chemistry can further be understood, in accordance with

one embodiment of the present invention. Wafer front side and backside 102a and 102b are cleaned and/or dried by front and back proximity heads 110a and 110b while front and back proximity heads 110a and 110b move in a movement direction 144 along a radius of the wafer 102 using a front and a back ~~meniscus~~ menisci 150 and 152. As used herein, the portion of fluids (e.g., front chemistry, rinse fluid, IPA vapor, etc.) defined in the region between the front proximity head 110a and the wafer front side 102a is defined as the front menisci 150. In the same manner, the back meniscus 152 is generated using the back cleaning chemistry, if any, or DIW and IPA vapor.

Page 26, para 71:

[0071] The plurality of front cleaning chemistry inlets 154 are defined substantially in the middle of the front proximity head 110a forming a substantially linear line designed to introduce ~~front cleaningchemistry inflow~~ liquid 146 onto the wafer front side 102a. Bordering the front cleaning chemistry inlets 154 is a plurality of vacuum ~~inlets~~ outlets 158 designed to vacuum and eliminate contaminants and any type of fluid defined between the vacuum ~~inlets~~ outlets 158 and the wafer front side 102a. As can further be seen, a plurality of isopropyl alcohol (IPA) inlets 156 are defined bordering the vacuum ~~inlets~~ outlets 158, which in the embodiment shown in Figure 4A, define an elliptic path. In the illustrated embodiment, the front meniscus 150 is formed in an area confined within the elliptical path of the vacuum ~~inlets~~ outlets 158.

Page 27, para 74:

[0074] With respect to the back proximity head 120b, the at least one IPA vapor inlet ~~158~~ 156 can be defined adjacent to the at least one vacuum outlet ~~156~~ 158, which is in turn is defined adjacent to the at least one DIW inlet 160 so as to form an IPA-vacuum-DIW

orientation. It must be noted by one of ordinary skill in the art that other types of orientations such as IPA-DIW-vacuum, DIW-vacuum-IPA, vacuum-IPA-DIW, etc. may be utilized depending on the wafer processes desired and type of wafer cleaning and/or drying mechanism being enhanced. In one preferred embodiment, the IPA-vacuum-DIW orientation is used to intelligently and powerfully generate, control, and move the back meniscus 152 located between the back proximity heads 110b and the wafer backside 102b. In another embodiment, IPA-vacuum orientation can be used to clean and/or dry wafer front and back sides 102a and 102b.

Page 27, para 75:

[0075] Still further, it must be noted that DIW inlets 160, the IPA vapor inlets ~~158~~ 156, the vacuum outlets ~~156~~ 158, and front cleaning chemistry and back cleaning chemistry inlets may be arranged on the top surface of the front and back proximity heads 110a and 110b in any suitable manner so long as respective meniscus can be generated and controlled. For example, in addition to the front cleaning chemistry inlet, IPA vapor inlet, the vacuum outlet, and the DIW inlet, in an additional embodiment, there may be additional sets of IPA vapor outlets, DIW inlets and/or vacuum outlets depending on the configuration of the proximity head desired.